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## INFORMATION DISCLOSURE STATEMENT

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APPLICANT:

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## U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE, IF APPROPRIAT E
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						

## FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION YES NO	
MAA	AH	2000-22212	1/21/00	Japan			Abstract	
MAA	AI	2000-12900	1/14/00	Japan			Abstract	
MAA	AJ	2000-44400	2/15/00	Japan			Abstract	
MAA	AK	11-340576	12/10/99	Japan			Abstract	
MAA	AL	2001-102307	4/13/01	Japan			Abstract	
MAA	AM	2002-29897	1/29/02	Japan			Abstract	
	AN							
	AO							
	AP							

## OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

MAA	AQ	Invitation Thesis, Collection of Theses of Electronic Information Communication Society C-II Vol. J81-C-II No. 1 pp. 58-64, January, 1998 "Thick Layer Growth of GaN by Hydride Vapor Phase Epitaxy", Akira Usui
MAA	AR	Preparation of Large Freestanding GaN Substrates by Hydride Vapor Phase Epitaxy Using GaA as a Starting Substrate, Jpn. J. Appl. Phys. Vol. 40 (2001) pp. L140-L143, Part 2, No. 2B, 15 February 2001
	AS	
	AT	
EXAMINER: Matthew A. C. [Signature]		DATE CONSIDERED: 9/9/03